

General Description

The WST2309 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST2309 meet the RoHS and Green Prod uct requirement with full function reliability appro ved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

BVDSS	RDSON	ID	
-60V	165mΩ	-2.8A	

Applications

- High Frequency Point-of-Load Synchronous
 Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25℃	Continuous Drain Current, -V _{GS} @ -10V ¹	-2.8	А
I _D @T _A =70°C	Continuous Drain Current, -V _{GS} @ -10V ¹	-1.8	Α
I _{DM}	Pulsed Drain Current ²	-8.4	А
P _D @T _C =25℃	Total Power Dissipation ³	1.5	W
T _{STG}	Storage Temperature Range -55 to 150		$^{\circ}$
T _J	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit	
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		125		
R _{eJC}	Thermal Resistance Junction-Case ¹		80	°C/W	

P-Channel MOSFET

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25℃ , I _D =-1mA		-0.021		V/°C
В	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-1.5A		165	200	mΩ
R _{DS(ON)}		V _{GS} =-4.5V , I _D =-1A		200	260	
$V_{GS(th)}$	Gate Threshold Voltage	V V I 050 A	-1.1	-1.7	-2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=-250uA$		4.08		mV/℃
	Drain Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =25°C			1	uA
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-48V , V_{GS} =0V , T_J =55 $^{\circ}$ C			5	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20 V$, V_{DS} = $0 V$			±100	nA
gfs	Forward Transconductance	V _{DS} =-10V , I _D =-1.5A		5.5		S
Q_g	Total Gate Charge (-4.5V)			4.6		
Q_gs	Gate-Source Charge	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-1.5A		1.4		nC
Q_gd	Gate-Drain Charge			1.6		
T _{d(on)}	Turn-On Delay Time			17.4		
T _r	Rise Time	V_{DD} =-15V , V_{GS} =-10V , R_{G} =3.3 Ω ,		5.4		20
T _{d(off)}	Turn-Off Delay Time	I _D =-1A		37.2		ns
T _f	Fall Time			2.4		
C _{iss}	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		456		
Coss	Output Capacitance			59		pF
C _{rss}	Reverse Transfer Capacitance			38		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current			-2.8	Α
I _{SM}	Pulsed Source Current ^{2,4}	V _G -V _D -UV , Force Current			-7.1	Α
V _{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_{S} =-1A , T_{J} =25 $^{\circ}$ C			-1.2	V

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300 us , duty cycle $\leq 2\%$ 3.The power dissipation is limited by 150 $^{\circ}$ C junction temperature
- 4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

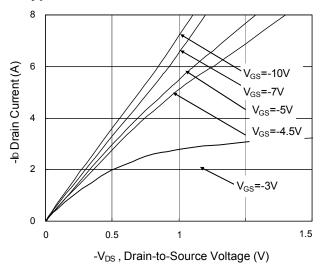


Fig.1 Typical Output Characteristics

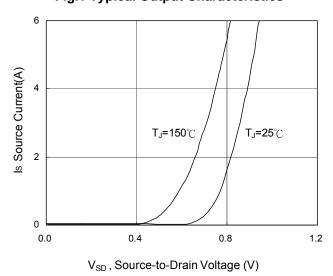


Fig.3 Forward Characteristics Of Reverse

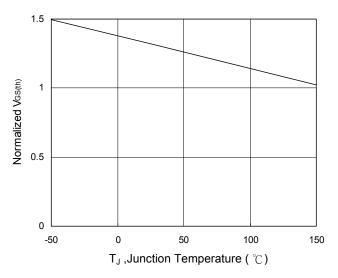


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

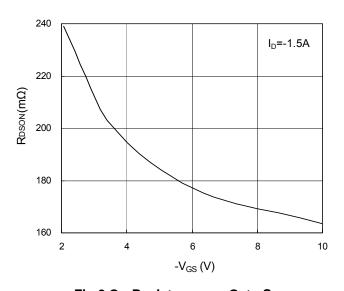


Fig.2 On-Resistance v.s Gate-Source

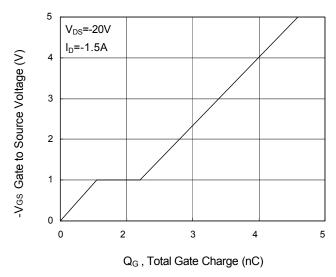


Fig.4 Gate-Charge Characteristics

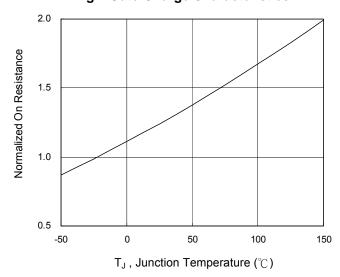
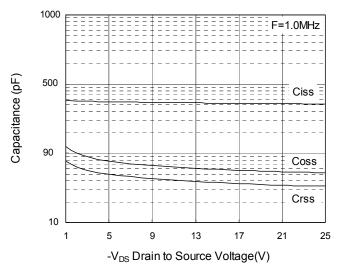


Fig.6 Normalized R_{DSON} v.s T_J







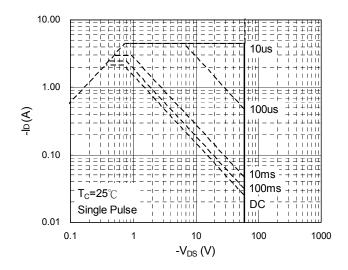


Fig.7 Capacitance

Fig.8 Safe Operating Area

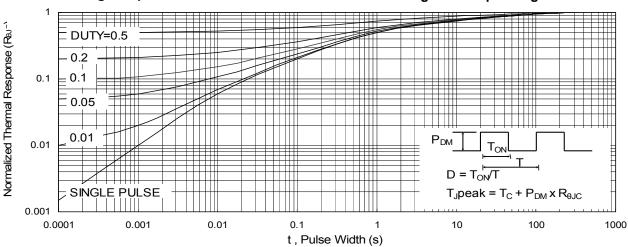
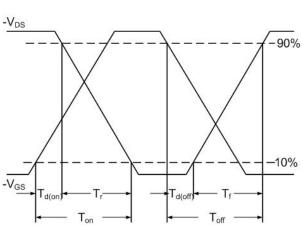
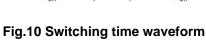


Fig.9 Normalized Maximum Transient Thermal Impedance





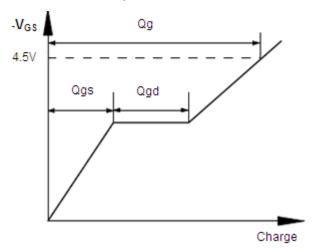


Fig.11 Gate Charge waveform



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DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7
DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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